

## **General Description**

This product family offers state of the art performance. It is designed for high frequency applications where high efficiency and high reliability are required.

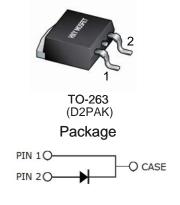
#### **Features**

- Low conduction loss due to low VF
- Extremely low switching loss by tiny Qc
- Highly rugged due to better surge current
- Industrial standard quality and reliability

### **Applications**

- UPS
- Power Inverter
- High performance SMPS
- Power factor correction

| Ordering Part<br>Number | Package       | Qty(PCS) |  |
|-------------------------|---------------|----------|--|
| HNXPSC10650B6J          | TO-263(D2PAK) | 800      |  |





# **Maximum Ratings** (at Tj = 25 °C, unless otherwise specified)

| Parameter  | Symbol           | Value          | Unit |  |
|--|------------------|----------------|------|--|
| Repetitive Peak Reverse Voltage  | Vrrm             | 650            | V    |  |
| Surge Peak Reverse Voltage   | Vrsm             | 650            | V    |  |
| DC Peak Reverse Voltage  | VR               | 650            | V    |  |
| Continuous Forward Current  Tc = 25°C  Tc = 135°C  Tc = 160°C  | lF               | 30<br>15<br>10 | А    |  |
| Repetitive Peak Forward Surge Current $Tc = 25^{\circ}C, t_{p} = 10 \text{ms}, \text{Half Sine Pulse}$ $Tc = 110^{\circ}C, t_{p} = 10 \text{ms}, \text{Half Sine Pulse}$ | IFRM             | 45<br>27       | А    |  |
| Non-Repetitive Forward Surge Current $Tc = 25^{\circ}C, t_p = 10 \text{ms}, \text{Half Sine Pulse}$ $Tc = 110^{\circ}C, t_p = 10 \text{ms}, \text{Half Sine Pulse}$      | IFSM             | 80<br>70       | А    |  |
| $i^2$ dt value $T_C = 25^{\circ}C, t_p = 10 ms, Half Sine Pulse$ $T_C = 110^{\circ}C, t_p = 10 ms, Half Sine Pulse$  | ∫ i²dt           | 31.7<br>24.3   | A²s  |  |
| Power dissipation $Tc = 25^{\circ}C$ $Tc = 110^{\circ}C$   | P <sub>tot</sub> | 92<br>40       | W    |  |
| Operating junction Range   | Tj               | -55 to +175    | °C   |  |
| Storage temperature Range  | Tstg             | -55 to +150    | °C   |  |

### **Thermal Resistance**

| Parameter                            | Symbol | Value | Unit |
|--------------------------------------|--------|-------|------|
| Thermal resistance, junction - case. | RthJC  | 1.62  | °C/W |

### Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

| Parameter               | Symbol | Value |      |      | Unit | Test Condition                           |  |
|-------------------------|--------|-------|------|------|------|--|--|
| i arameter              | Oymboi | min.  | typ. | max. | Oill | rest Condition                           |  |
| Forward Voltage         | VF     |       |      |      | ٧    | I <sub>F</sub> =10A                      |  |
|                         |        | -     | 1.3  | 1.5  |      | T <sub>j</sub> =25°C                     |  |
|                         |        | -     | 1.6  | -    |      | Tj=175°C                                 |  |
| Reverse Current         |        |       |      |      | μΑ   | Vr=650V                                  |  |
|                         | lR     | -     | -    | 50   |      | T <sub>j</sub> =25°C                     |  |
|                         |        | -     | -    | 200  |      | T <sub>j</sub> =175°C                    |  |
| Total Capacitive Charge | Qc     | -     | 27   |      | nC   | V <sub>R</sub> =400V,T <sub>j</sub> =25℃ |  |
|                         |        |       |      | -    |      | $Q_C = \int_0^{V_R} C(V) dV$             |  |
| Total Capacitance       | С      |       |      |      | pF   | Tj=25℃, f=1MHz                           |  |
|                         |        | -     | 561  | -    |      | V <sub>R</sub> =0V                       |  |
|                         |        | -     | 55   | -    |      | V <sub>R</sub> =200V                     |  |
|                         |        | -     | 43   | -    |      | V <sub>R</sub> =400V                     |  |

#### **Characteristics Curve:**

Fig 1: Forward Characteristics

20

T<sub>j=25°C</sub>

T<sub>j=175°C</sub>

T<sub>j=175°C</sub>

T<sub>j=175°C</sub>

T<sub>j=175°C</sub>

V<sub>F</sub> (V)

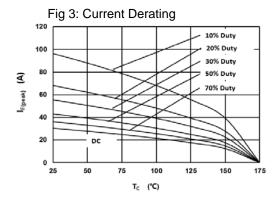
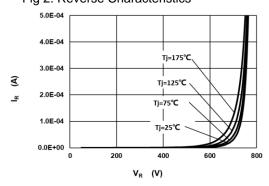


Fig 2: Reverse Characteristics



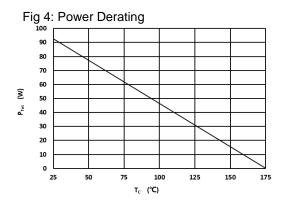


Fig. F. Conneitance va. Bayeree Valtage

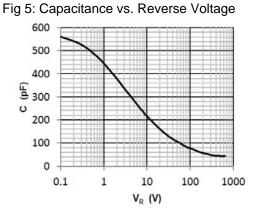


Fig 6: Reverse Charge vs. Reverse Voltage

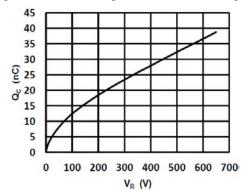


Fig 7: Typical Capacitance Stored Energy

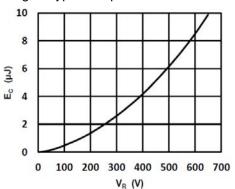
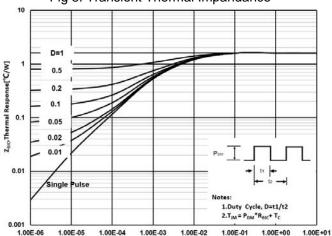
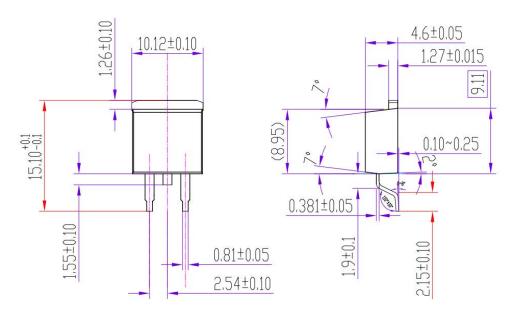


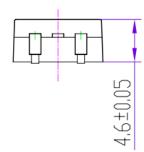
Fig 8: Transient Thermal Impandance

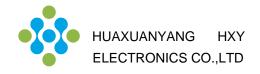


## **Package Dimensions**

Package TO-263(D2PAK)







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